

Title (en)
Semiconductor integrated circuit and its manufacturing method

Title (de)
Integrierte Halbleiterschaltung und Verfahren zu deren Herstellung

Title (fr)
Circuit intégré à semi-conducteur et procédé pour sa fabrication

Publication
EP 1326288 A3 20041117 (EN)

Application
EP 02258802 A 20021219

Priority
JP 2001398200 A 20011227

Abstract (en)
[origin: EP1326288A2] A method for manufacturing a semiconductor integrated circuit includes steps of forming a semiconductor element on a semiconductor substrate and separating only a function layer including the semiconductor element, which is a surface layer of the semiconductor substrate, from the semiconductor substrate. The semiconductor element is preferably a compound semiconductor device including at least one of a light emitting diode, a vertical cavity surface emitting laser diode, a photodiode, a high electron mobility transistor, an inductor, a capacitor, a resistor, and a heterojunction bipolar transistor. <IMAGE>

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H01L 31/18; H01L 21/20; H01L 33/00

IPC 8 full level
H01L 21/331 (2006.01); **H01L 21/02** (2006.01); **H01L 21/20** (2006.01); **H01L 21/306** (2006.01); **H01L 21/336** (2006.01); **H01L 21/338** (2006.01); **H01L 21/60** (2006.01); **H01L 27/12** (2006.01); **H01L 27/15** (2006.01); **H01L 29/737** (2006.01); **H01L 29/778** (2006.01); **H01L 29/786** (2006.01); **H01L 29/812** (2006.01); **H01L 51/52** (2006.01)

CPC (source: EP US)
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C-Set (source: EP US)
1. **H01L 2224/92 + H01L 2224/83 + H01L 2224/82**
2. **H01L 2224/83192 + H01L 2224/32225**
3. **H01L 2924/0132 + H01L 2924/01015 + H01L 2924/01049**
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5. **H01L 2924/3512 + H01L 2924/00**
6. **H01L 2924/13064 + H01L 2924/00**
7. **H01L 2924/1305 + H01L 2924/00**
8. **H01L 2924/12043 + H01L 2924/00**

Citation (search report)
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